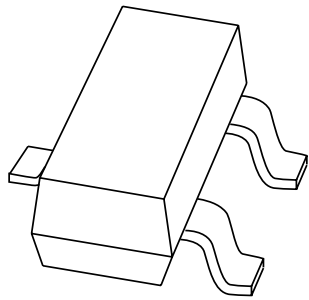


# DATA SHEET



## **BAS16** High-speed diode

Product specification  
Supersedes data of 1999 May 26

2001 Oct 10

# High-speed diode

# BAS16

### FEATURES

- Small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

### APPLICATIONS

- High-speed switching in hybrid thick and thin-film circuits.

### DESCRIPTION

The BAS16 is a high-speed switching diode fabricated in planar technology, and encapsulated in a small SOT23 plastic SMD package.

### MARKING

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
BAS16	A6*

### Note

1. \* = p : Made in Hong Kong.  
 \* = t : Made in Malaysia.  
 \* = W : Made in China.

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{RRM}$	repetitive peak reverse voltage		–	85	V
$V_R$	continuous reverse voltage		–	75	V
$I_F$	continuous forward current	see Fig.2; note 1	–	215	mA
$I_{FRM}$	repetitive peak forward current		–	500	mA
$I_{FSM}$	non-repetitive peak forward current	square wave; $T_j = 25\text{ °C}$ prior to surge; see Fig.4 $t = 1\ \mu\text{s}$ $t = 1\ \text{ms}$ $t = 1\ \text{s}$	–	4 1 0.5	A A A
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ °C}$ ; note 1	–	250	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C

### Note

1. Device mounted on an FR4 printed-circuit board.

### PINNING

PIN	DESCRIPTION
1	anode
2	not connected
3	cathode

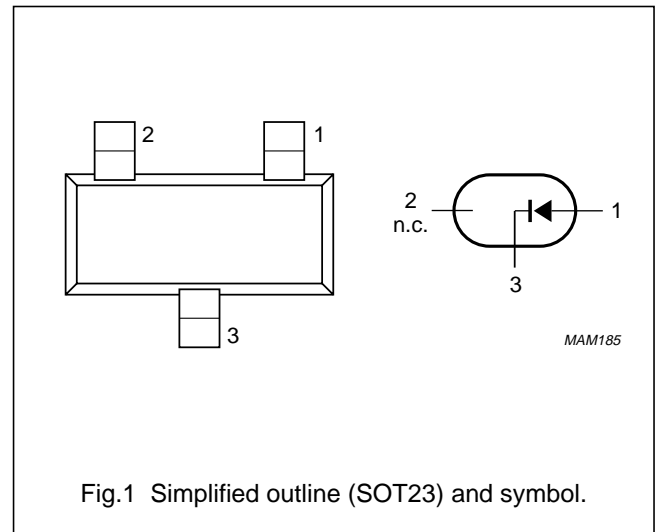


Fig.1 Simplified outline (SOT23) and symbol.

## High-speed diode

## BAS16

**ELECTRICAL CHARACTERISTICS**

$T_j = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
$V_F$	forward voltage	see Fig.3		
		$I_F = 1\text{ mA}$	715	mV
		$I_F = 10\text{ mA}$	855	mV
		$I_F = 50\text{ mA}$	1	V
$I_R$	reverse current	see Fig.5		
		$V_R = 25\text{ V}$	30	nA
		$V_R = 75\text{ V}$	1	$\mu\text{A}$
		$V_R = 25\text{ V}; T_j = 150\text{ °C}$	30	$\mu\text{A}$
		$V_R = 75\text{ V}; T_j = 150\text{ °C}$	50	$\mu\text{A}$
$C_d$	diode capacitance	$f = 1\text{ MHz}; V_R = 0$ ; see Fig.6	1.5	pF
$t_{rr}$	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}; R_L = 100\ \Omega$ ; measured at $I_R = 1\text{ mA}$ ; see Fig.7	4	ns
$V_{fr}$	forward recovery voltage	when switched from $I_F = 10\text{ mA}; t_r = 20\text{ ns}$ ; see Fig.8	1.75	V

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point		330	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

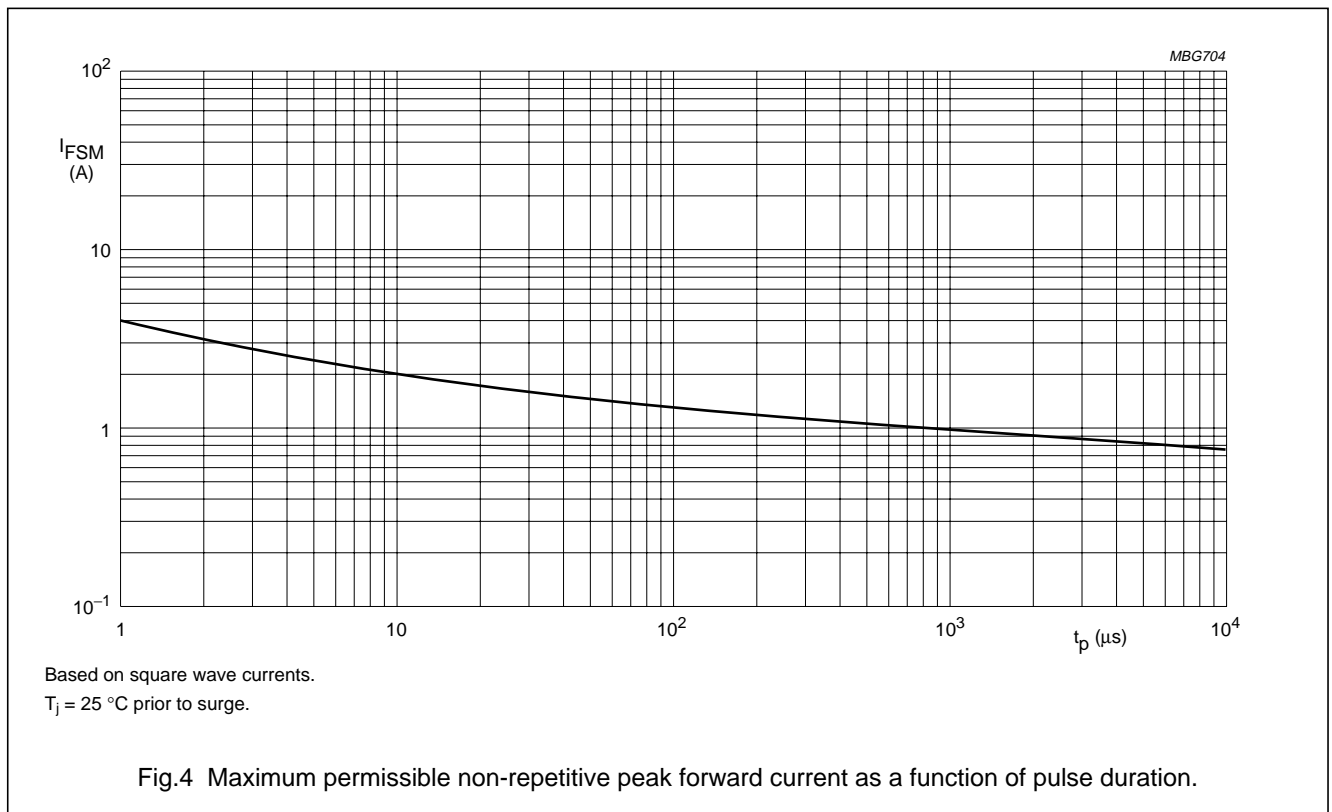
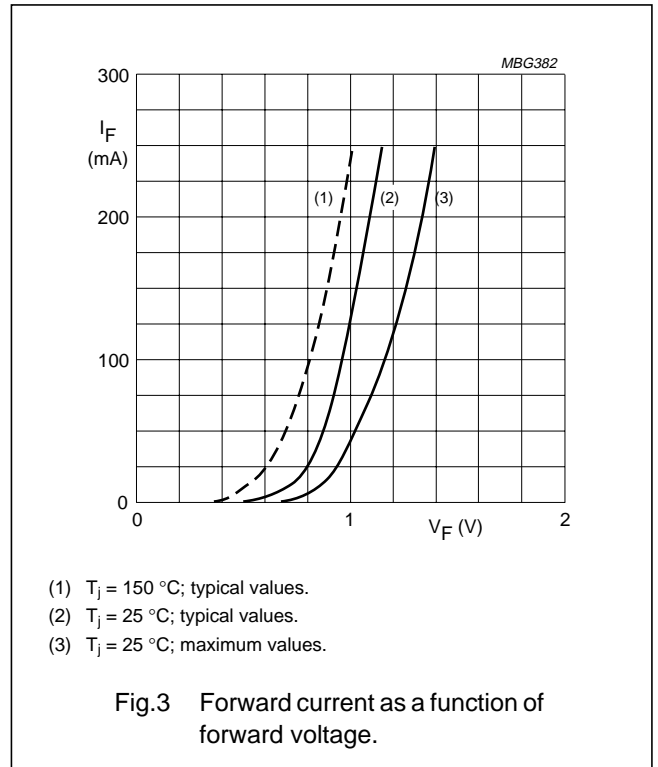
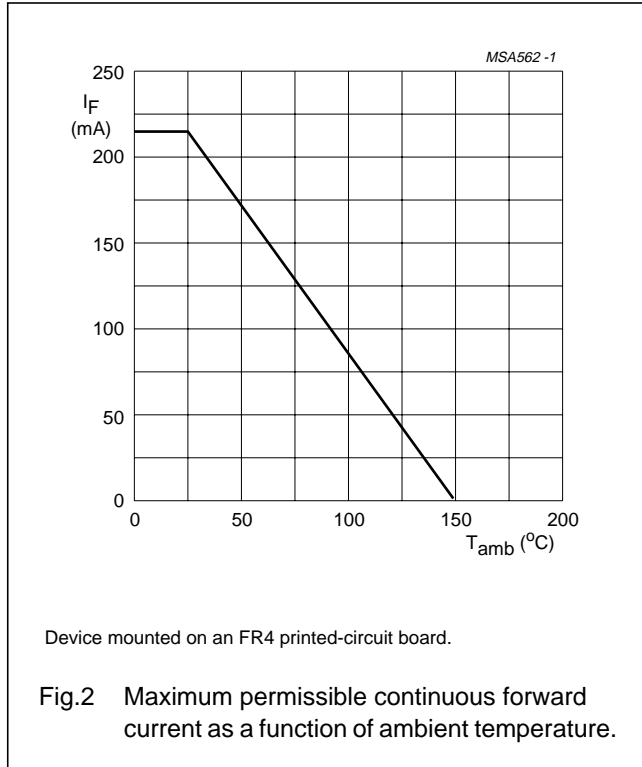
**Note**

1. Device mounted on an FR4 printed-circuit board.

High-speed diode

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GRAPHICAL DATA



High-speed diode

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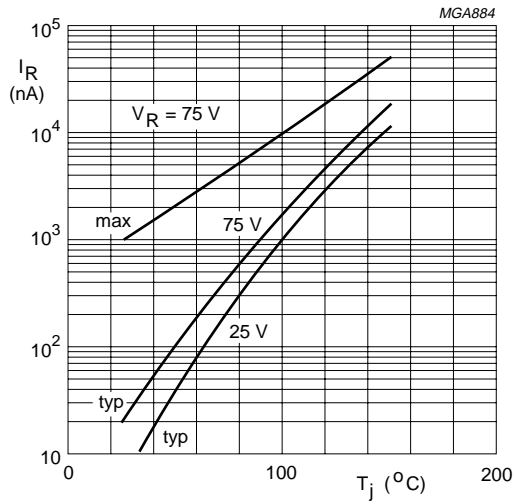
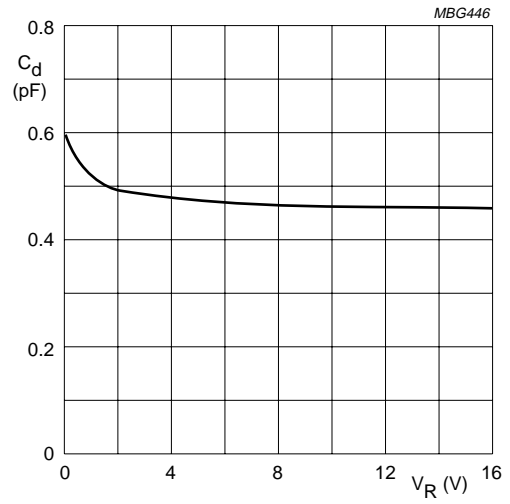


Fig.5 Reverse current as a function of junction temperature.

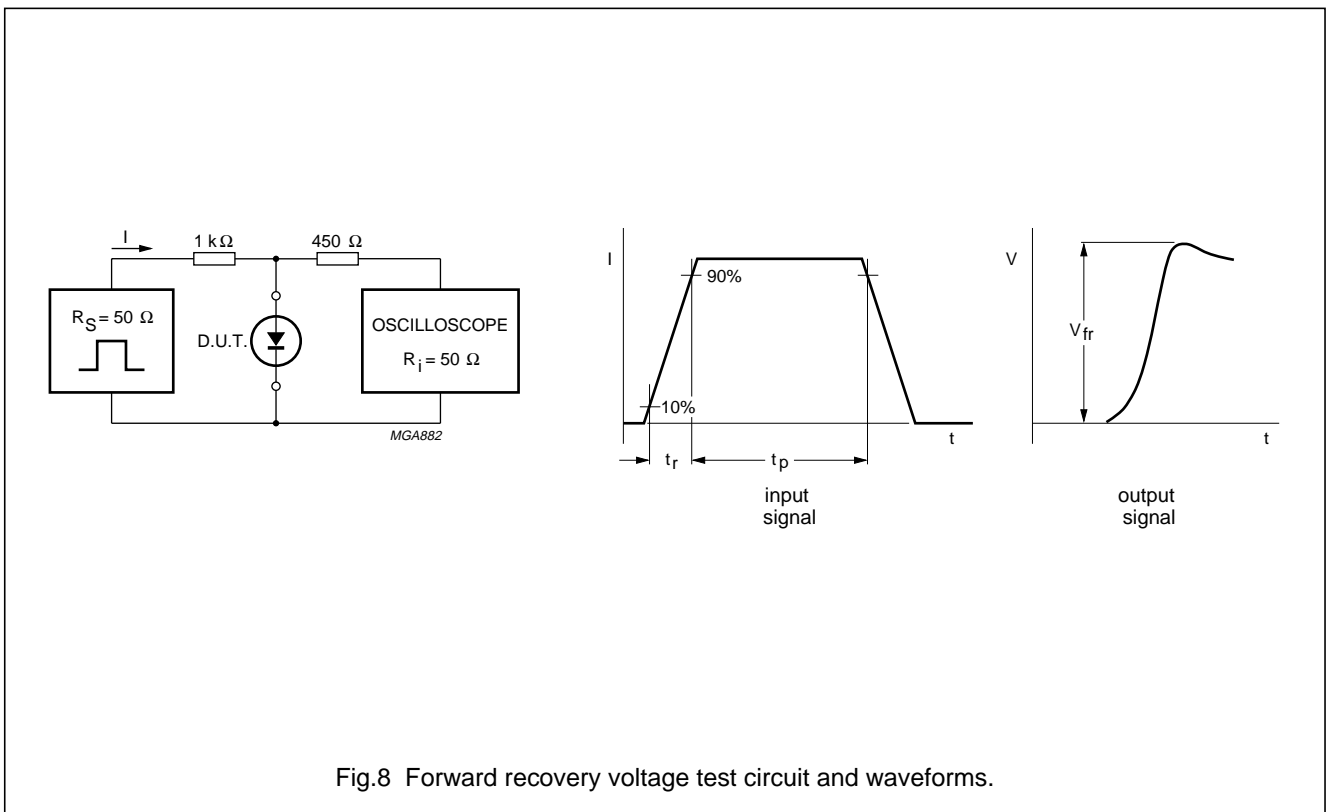
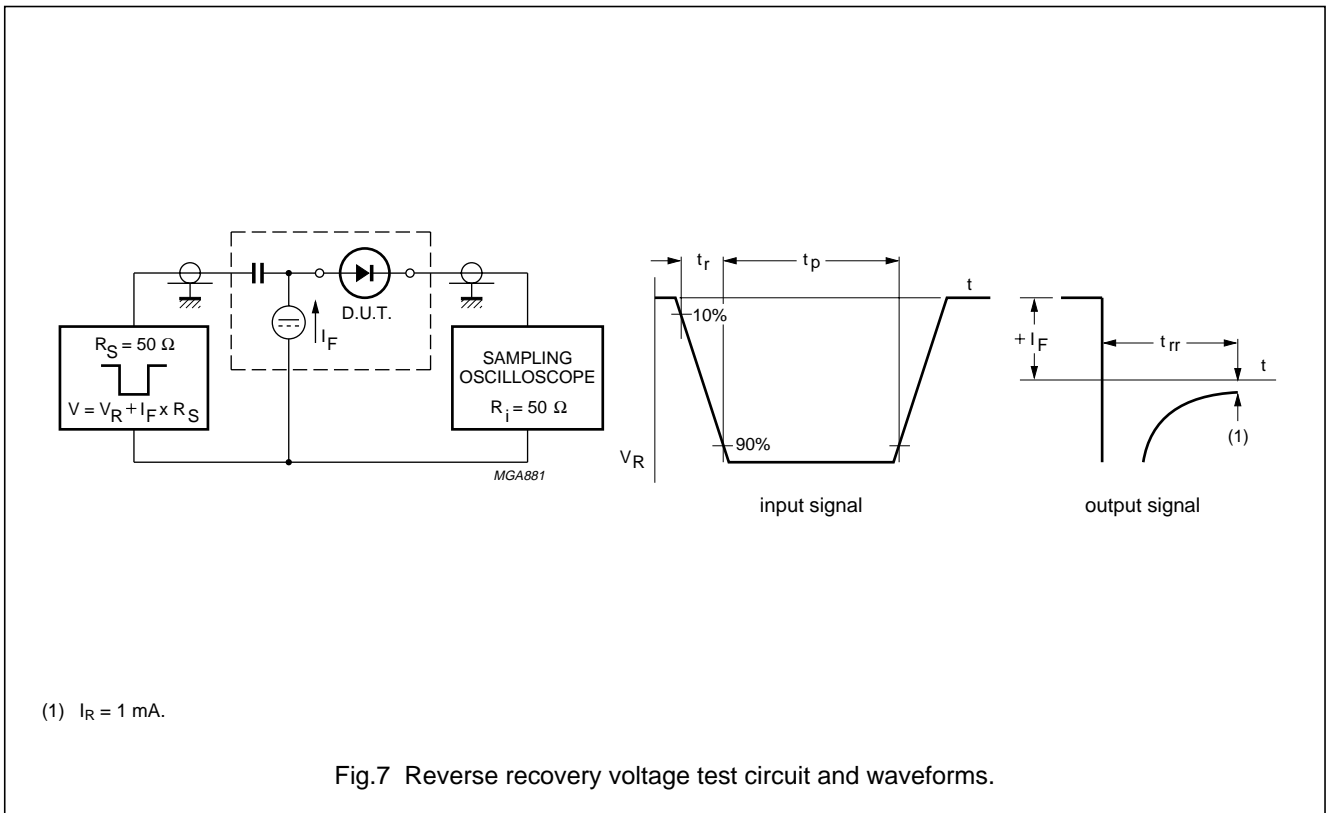


$f = 1$  MHz;  $T_j = 25$  °C.

Fig.6 Diode capacitance as a function of reverse voltage; typical values.

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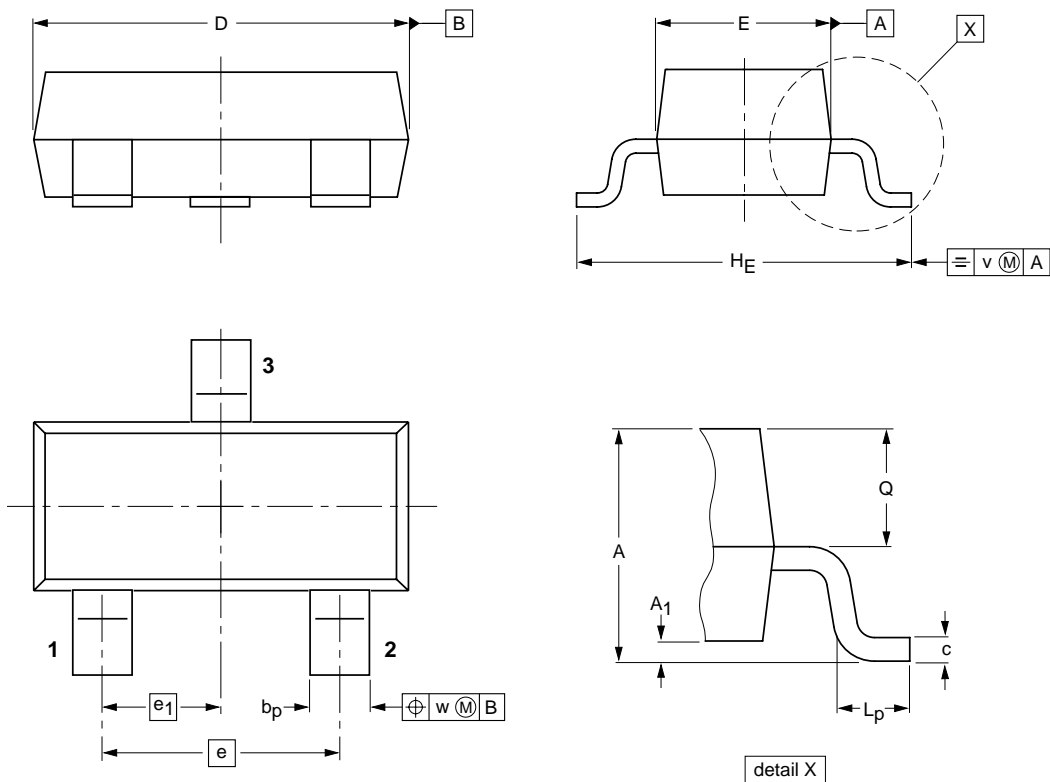
# High-speed diode

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## PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



**DIMENSIONS (mm are the original dimensions)**

UNIT	A	A <sub>1</sub> max.	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT23		TO-236AB			97-02-28 99-09-13

## High-speed diode

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## DATA SHEET STATUS

DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
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**NOTES**

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**NOTES**

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**NOTES**

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